The Sustainable Way of Life…..

156mm x 156mm Multicrystalline Silicon Wafers

Technical Specifications

PV-W156MUM	
	
Crystal Type:	multicrystalline silicon
Growth Method:	directional solidification
Conductivity Type:	(Boron Doped),ASTM F42
Carbon:	< 4 x 1017 cm-3, ASTM F 121
Oxygen:	< 1 x 1018 cm-3, ASTM F 121
Crystal structure:	multicrystalline vertically directed crystallites
Parameters of Wafers	
Wafer Square side:	156 x 156 ± 0,5 mm
Side orientation:	90°± 0.5°
Bevel edge width:	1.0 -2.0 mm
Thickness of wafer:	200 µm ± 30 µm, ASTM F 533
TTV:	< 50 µm, ASTM F 657
BOW:	< 50 µm, ASTM F 534
Saw grooves:	< 20 µm (depth) (< 15 typically)
Resistivity:	0.5 -3.0 Ohm.cm, ASTM F43
Lifetime:	2 µs, ASTM F 28
Surface:	as-cut and cleaned; visible contamination, oil or grease, finger prints, soap stains, slurry stains, epoxy/water stains, cracks are not allowed; edge chips under 1 mm from the edge of the wafer are allowed.